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NXP Semiconductors/Freescale Semiconductor, Inc. PMPB43XPE,115

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Datasheet of PMPB43XPE,115 - MOSFET P-CH 20V 5A 6DFN

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Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- 1 kV ESD protected
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

3. Applications

- Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portable devices
- · Hard disk and computing power management

4. Quick reference data

Table 1. Quick reference data

| Table 1. Quiek reference data | | | | | | | |
|-------------------------------|----------------------------------|--------------------------------------------------------------------|-----|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| V_{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V_{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | - | -5 | Α |
| Static characte | Static characteristics | | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = -4.5 \text{ V}; I_D = -5 \text{ A}; T_j = 25 \text{ °C}$ | | - | 39 | 48 | mΩ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².







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20 V, single P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|-----------------------|----------------|
| 1 | D | drain | 1 6 | D I |
| 2 | D | drain | 7 7 | |
| 3 | G | gate | | G T |
| 4 | S | source | 3 8 4 | |
| 5 | D | drain | Transparent top view | 17 |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | S 017aaa259 |
| 7 | D | drain | | |
| 8 | S | source | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|-------------|-----------------------------------------------------------------------------------------------|---------|--|--|
| | Name | Description | Version | | |
| PMPB43XPE | DFN2020MD-6 | DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMPB43XPE | 1Y |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|-----------------------------------------------------|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V _{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -5 | Α |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -3.1 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs | | - | -12 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [1] | - | 1.7 | W |
| | | T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 3.5 | W |
| | | T _{sp} = 25 °C | | - | 12.5 | W |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain | diode | ' | ' | ' | ' | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | -1.9 | Α |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

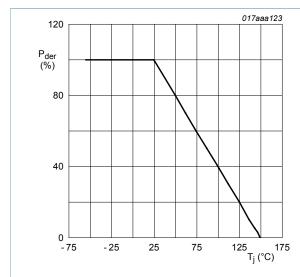


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

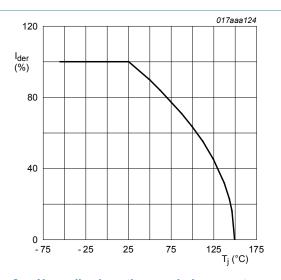


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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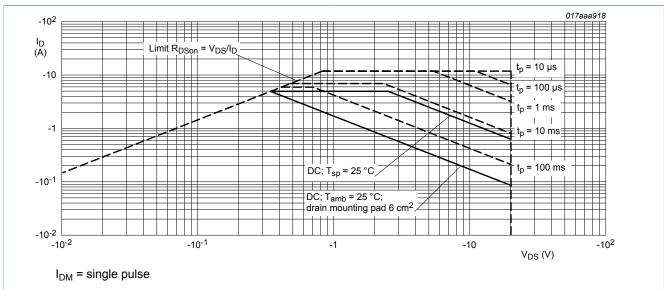
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Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-Fig. 3. source voltage

Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--------------------------------------------------------|----------------------|------------|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | | [1] | - | 235 | 270 | K/W |
| | | | <u>[2]</u> | - | 67 | 74 | K/W |
| | | in free air; t ≤ 5 s | <u>[2]</u> | - | 33 | 36 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 5 | 10 | K/W |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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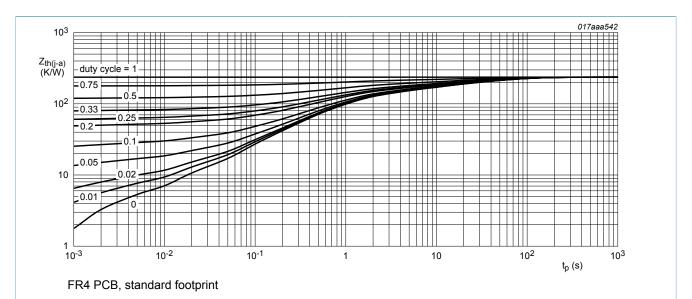
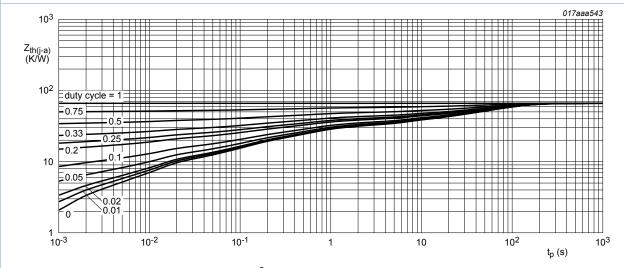


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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10. Characteristics

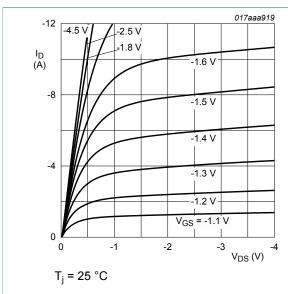
Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|-------------------------------------------------------------------------|-------|-------|------|------|
| Static cha | racteristics | | | | | , |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ | -0.47 | -0.68 | -0.9 | V |
| I _{DSS} | drain leakage current | V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C | - | - | -1 | μΑ |
| I _{GSS} | gate leakage current | V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -10 | μΑ |
| | | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 10 | μΑ |
| R _{DSon} | drain-source on-state | V_{GS} = -4.5 V; I_D = -5 A; T_j = 25 °C | - | 39 | 48 | mΩ |
| | resistance | V_{GS} = -4.5 V; I_D = -5 A; T_j = 150 °C | - | 55 | 68 | mΩ |
| | | V_{GS} = -2.5 V; I_D = -4.5 A; T_j = 25 °C | - | 45 | 59 | mΩ |
| | | V_{GS} = -1.8 V; I_D = -3.7 A; T_j = 25 °C | - | 56 | 79 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = -10 V; I_D = -5 A; T_j = 25 °C | - | 20 | - | S |
| R_G | gate resistance | f = 1 MHz | - | 5.6 | - | Ω |
| Dynamic c | characteristics | | | ' | | , |
| Q _{G(tot)} | total gate charge | V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V; | - | 15.6 | 23.4 | nC |
| Q_{GS} | gate-source charge | T _j = 25 °C | - | 1.9 | - | nC |
| Q_{GD} | gate-drain charge | | - | 3.4 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$ | - | 1550 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 142 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 116 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -10 V; I_{D} = -5 A; V_{GS} = -4.5 V; | - | 9 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 38 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 57 | - | ns |
| t _f | fall time | | - | 25 | - | ns |
| Source-dra | ain diode | 1 | 1 | | 1 | |
| V _{SD} | source-drain voltage | $I_S = -1.9 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | -0.7 | -1.2 | V |

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Output characteristics: drain current as a Fig. 6. function of drain-source voltage; typical values

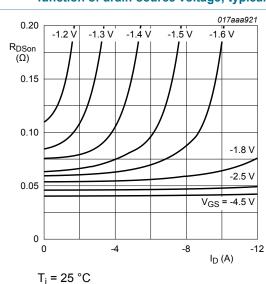
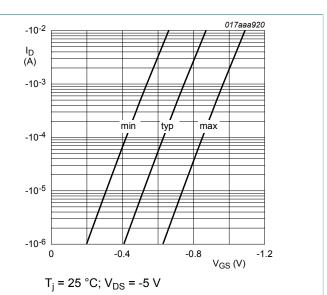


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



Sub-threshold drain current as a function of Fig. 7. gate-source voltage

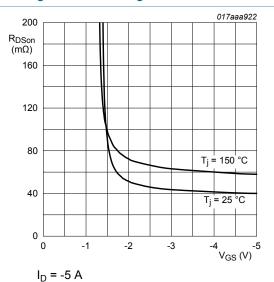


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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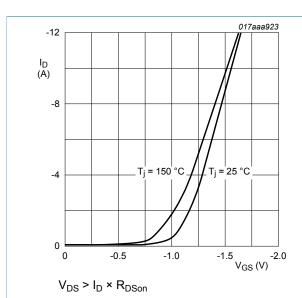


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

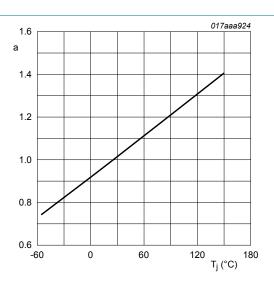


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon/259O}}$$

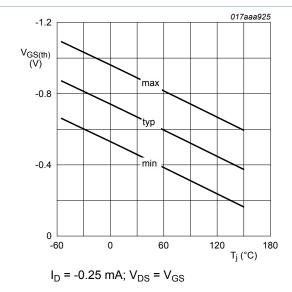


Fig. 12. Gate-source threshold voltage as a function of junction temperature

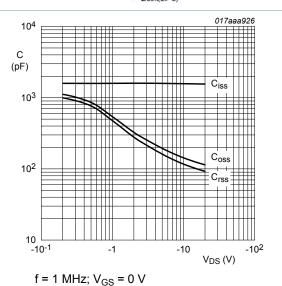
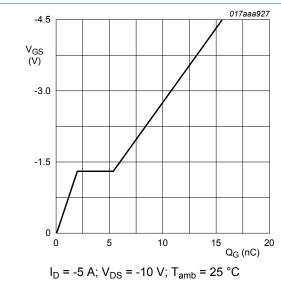


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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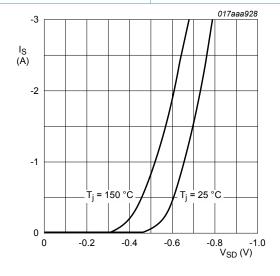
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 V_{DS} $V_{GS(pl)}$ V_{GS(th)} V_{GS} Q_{GS1} Q_{GS2} QGS Q_{GD}-Q_{G(tot)}-017aaa137

Fig. 15. MOSFET transistor: Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$

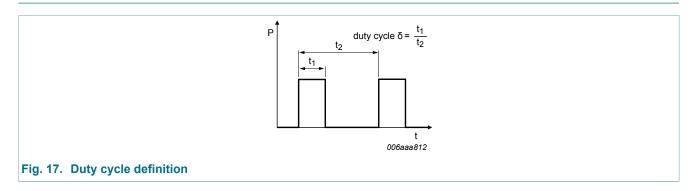
Fig. 16. Source current as a function of source-drain voltage; typical values



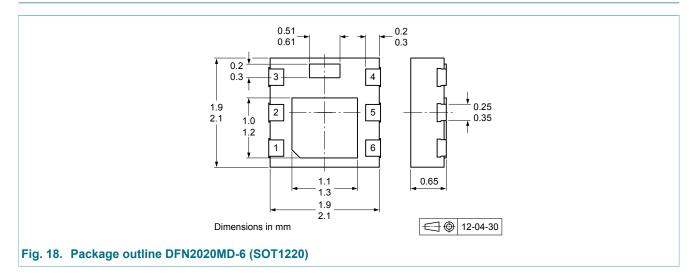
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11. Test information



12. Package outline

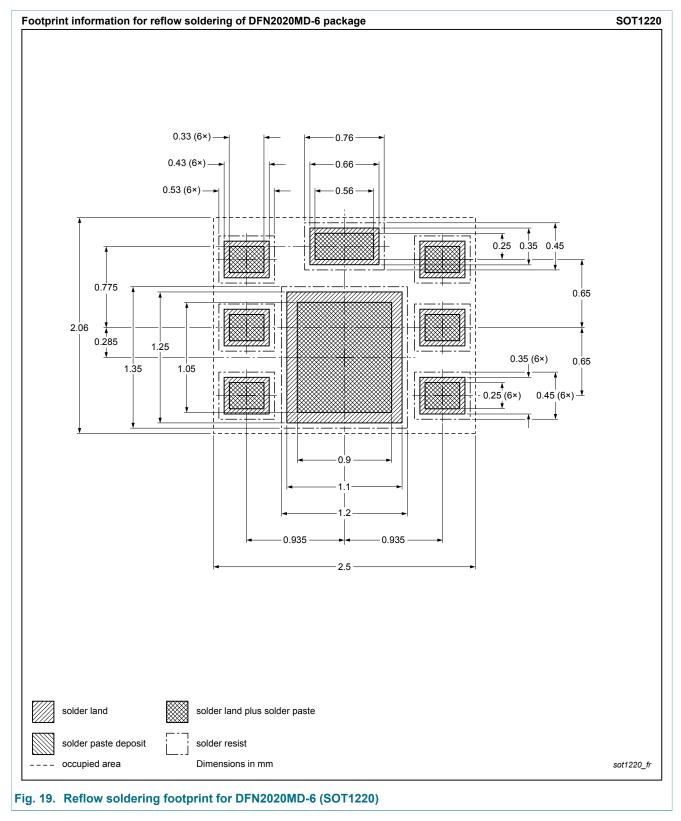




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13. Soldering



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14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|---------------------------------------------------------------------------------------------|--------------------|---------------|---------------|
| PMPB43XPE v.2 | 20141126 | Product data sheet | - | PMPB43XPE v.1 |
| Modifications: | 3D package outline Features and benef Table 5: updated | | | |
| PMPB43XPE v.1 | 20121130 | Product data sheet | - | - |



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15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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